IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Geoff W. Taylor et al. Group Art Unit: 2811

Serial No.: 10/602,218 Examiner:

Filed: June 24, 2003 Attorney Docket: OPE-029

Title: Heterojunction Thyristor-based Amplifier

I hereby certify that this correspondence is being deposited on this day with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Alexandria, VA 22313-1450.

David P. Gordon Dec 12, 2003

David P. Gordon Date

Honorable Commissioner for Patents
Alexandria, VA 22313

SUBMITTAL OF DOCUMENTS PURSUANT TO DUTY OF DISCLOSURE

Pursuant to applicant's duty of disclosure 37 CFR Section 1.56, enclosed is a completed form PTOL-1449 as well as copies of the cited documents that relate to the above-referenced patent application. Since this document submittal is being presented prior to the first examination on the merits, no fee is due herewith.

The listed documents are brought to the Examiner's attention because they are known to the applicant and/or the applicant's attorney and may be considered by the Examiner to be material to his/her examination. This listing should not be construed as representation that a search has been made or that no better art exists. No inference should be made that the documents are in fact material merely because they are referenced herein. Moreover, no representation is made that the brief descriptions of the references herein necessarily describe the most material aspects of the references. Further, by this listing, the applicant is not making any admission regarding the relative dates of the invention and listed disclosures.

Respectfully submitted,

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| INFORMATION DISCLOSURE CITATION<br><br>PAGE 1 OF 2 | Atty Docket No.<br>OPE-029 | Serial No.<br>10/602,218 |
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| INFORMATION DISCLOSURE CITATION<br><br>PAGE 2 OF 2 | Atty Docket No.<br>OPE-029 | Serial No.<br>10/602,218 |
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